

Amendment**Claim Amendments**

1. (currently amended) A multiple input ESD protection structure comprising
 - a first p-well formed in a first n-well,
 - a second p-well formed in a second n-well,
 - an isolation ring between the n-wells and extending around the two n-wells, the isolation ring comprising a p⁺ ring,
 - a first input region formed in the second p-well,
 - a second input region formed in the second p-well,
 - a contact to the first input region,
 - a contact to the second input region, and
 - a contact to the isolation ring, wherein the first and second input regions each comprises at least one of an n⁺ region and a p⁺ region.
2. (canceled)
3. (withdrawn) A structure of claim 1, wherein the isolation ring takes the form of two adjacent p⁺ rings.
4. (withdrawn) A structure of claim 3, wherein a n⁺ ring is formed between the p⁺ rings.
5. (original) A structure of claim 2, wherein the isolation ring is formed in a p-well.
6. (original) A structure of claim 5, wherein a p-buried layer (PBL) is formed below the p-well of the isolation ring.
7. (withdrawn) A structure of claim 4, wherein the p-rings are formed in a p-well.
8. (withdrawn) A structure of claim 7, wherein a p-buried layer (PBL) is formed below the p-well of the isolation ring.
9. (original) A structure of claim 1, further comprising an n-isolation region (NISO) formed beneath at least one of the n-wells.
10. (original) A structure of claim 9, further comprising a p-buried layer (PBL) formed beneath at least one of the first and second p-wells.
11. (withdrawn) A structure of claim 4, further comprising an n-isolation region (NISO) formed beneath at least one of the n-wells.

12. (withdrawn) A structure of claim 11, further comprising a p-buried layer (PBL) formed beneath at least one of the first and second p-wells.
13. (original) A structure of claim 1, wherein at least one of the first and second input regions includes a p⁺ region and an n⁺ region.
14. (withdrawn) A structure of claim 1, wherein the first input region includes only a p⁺ region or only a n⁺ region and the second input region includes both a n⁺ and a p⁺ region.
15. (withdrawn) A structure of claim 1, wherein the first input region includes only a p⁺ region and the second input region includes only an n⁺ region.
16. (withdrawn) A structure of claim 4, wherein at least one of the first and second input regions includes a p⁺ region and an n⁺ region.
17. (withdrawn) A structure of claim 4, wherein the first input region includes only a p⁺ region or only a n⁺ region and the second input region includes both a n⁺ and a p⁺ region.
18. (withdrawn) A structure of claim 4, wherein the first input region includes only a p⁺ region and the second input region includes only an n⁺ region.
19. (currently amended) An ESD protection device that comprises
 - a first p-well formed in a first n-well,
 - a second p-well formed in a second n-well,
 - an isolation ring between the n-wells and extending around the two n wells, the isolation ring comprising a p⁺ ring,
 - a first input region formed in the first p-well,
 - a second input region formed in the second p-well,
 - a contact to the first input region,
 - a contact to the second input region, and
 - a contact to the isolation ring, wherein the isolation ring is connected to ground or is biased to a predefined voltage wherein the first and second input regions each comprises at least one of an n⁺ region and a p⁺ region.
20. (withdrawn) A multiple input ESD protection structure, comprising
 - a first p-well formed in a first n-well,
 - a second p-well formed in a second n-well,
 - a first input region formed in the first p-well,

a second input region formed in the second p-well,

a contact to the first input region, and

a contact to the second input region, wherein one of the input regions is connected to ground and forms at least a partial isolation ring around the other input region.